



PVSEC-7 (1993) / Nagoya, Japan

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C-VIII-2	Externalities, Social Costing and Photovoltaic Power Development T. Takeshita Technova Inc., Japan
C-VIII-3	SPV Power Pack-Socio-Economic Impact for Rural Development S.Madan M.P. Energy Development Corporation, India

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■ **PVSystem-III**

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C-IX-2	Research and Development on Evaluation Technology of Photovoltaic Power Systems M.Yukawa and K.Kurokawa* JMI Institute, Japan *Electrotechnical Laboratory, Japan
C-IX-3	Test and Analysis of a Dispatchable, Commercial Building Photovoltaic-Demand Side Management System A.M.Bamett, W.R.Bottenberg, J.M.Beck, J.E.Cotter, R.M.Nigro*, J.Byrne**, Y.D.Wang**, E.C.Kern***, M.C.Russell***, H.Meyer ⁺ and R.Flemming ⁺⁺ AstroPower, Inc., U.S.A. *Delmarva Power and Light Company, U.S.A. **University of Delaware, U.S.A. ***Ascension Technology, Inc., U.S.A. +Omniion Power Engineering Corporation, U.S.A. ++AC Battery Corporation, U.S.A.
C-IX-4	Utility Distribution System Behavior during Islanding of Grid-Connected Residential PV Systems F.Yamamoto, M.Okamoto, S.Akita, A.Kitamura, K.Takigawa*, Y.Ariga*, T.Ishikawa* and H.Kobayashi* The Kansai Electric Power Co., Inc., Japan. *Central Res. Inst. of Electric Power Industry, Japan
C-IX-5	SCADA Application for Utility Scale Photovoltaic Systems L.Kendrick, Jr. and P.B.Rosen* Pacific Gas and Electric Co., U.S.A. *Endecon, U.S.A.
C-IX-6	Annual Simulation Results of PV System with Redox Flow Battery I.Tsuda, K.Kurokawa and K.Nozaki Electrotechnical Laboratory, Japan

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■ **Plenary Lecture -III**

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PL-III-2	The PV Era is Coming the Way to GENESIS Y. Kuwano Sanyo Electric Co., Ltd., Japan

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